

	No.3399C	2SA1773/2SC4616 2SA1773:PNP Epitaxial Planar Silicon Transistor 2SC4616:NPN Triple Diffused Planar Silicon Transistor High Voltage Driver Applications

Features

- Large current capacity ($I_C = 2A$)
- High blocking voltage ($V_{CEO} \geq 400V$)

() : 2SA1773

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector-to-Base Voltage	V_{CBO}	(-)400	V
Collector-to-Emitter Voltage	V_{CEO}	(-)400	V
Emitter-to-Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)2	A
Collector Current(Pulse)	I_{CP}	(-)4	A
Collector Dissipation	P_C	1	W
		15	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	- 55 to + 150	$^\circ C$

$T_c = 25^\circ C$

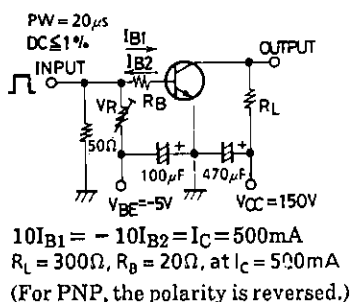
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)300V, I_E = 0$		(-)1.0		μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$		(-)1.0		μA
DC Current Gain	h_{FE}	$V_{CE} = (-)10V, I_C = (-)100mA$	40*		200*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10V, I_C = (-)100mA$	(40)60			MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)500mA, I_B = (-)50mA$		(-)1.0		V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)500mA, I_B = (-)50mA$		(-)1.0		V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)400			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)400			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V
Output Capacitance	C_{ob}	$V_{CB} = (-)30V, f = 1MHz$		(25)15		pF
Turn-ON Time	t_{on}	See specified Test Circuit.	(0.12)0.085			μs
Storage Time	t_{stg}	"	(3.0)4.0			μs
Fall Time	t_f	"	(0.3)0.6			μs

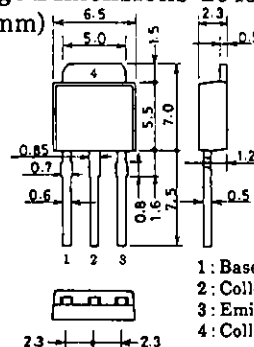
*: The 2SA1773/2SC4616 are classified by 100mA h_{FE} as follows:

40 C 80	60 D 120	100 E 200
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Switching Time Test Circuit

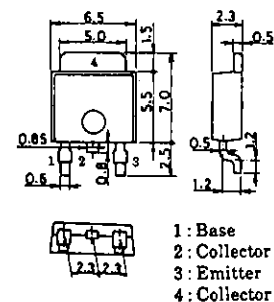


Package Dimensions 2045A (unit : mm)



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Package Dimensions 2044A (unit : mm)

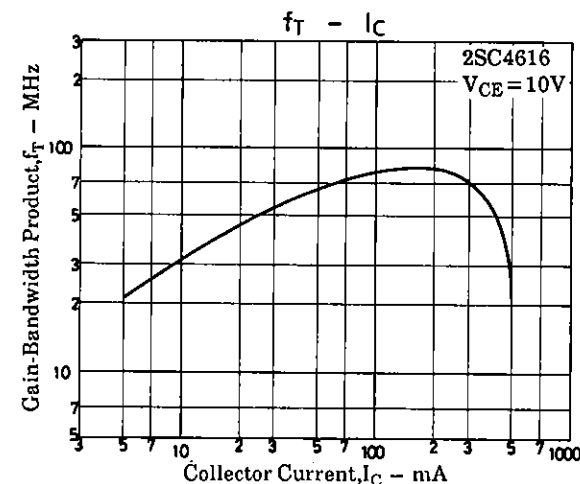
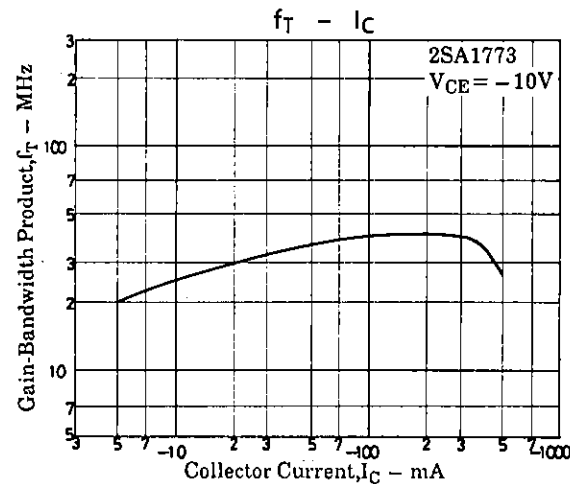
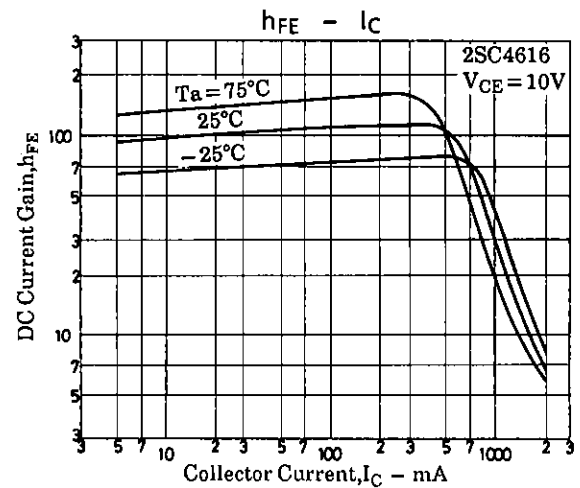
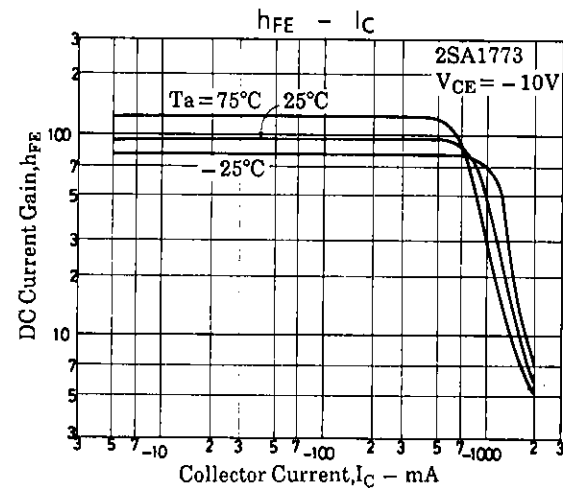
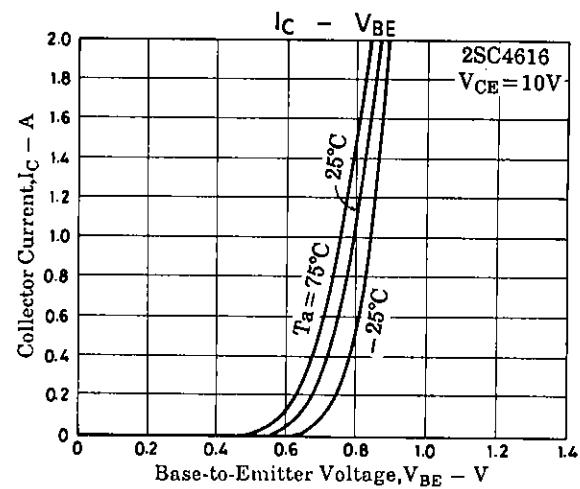
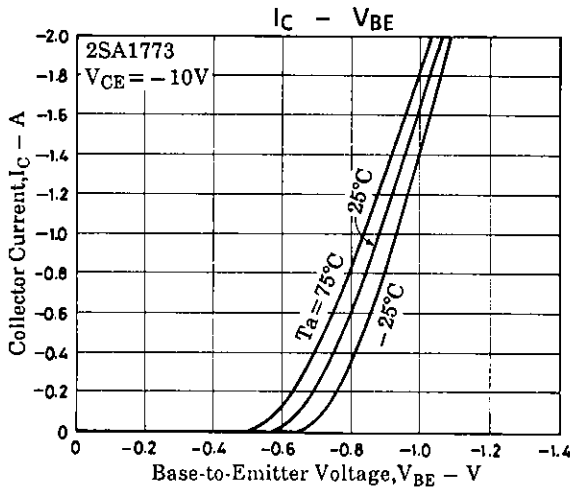
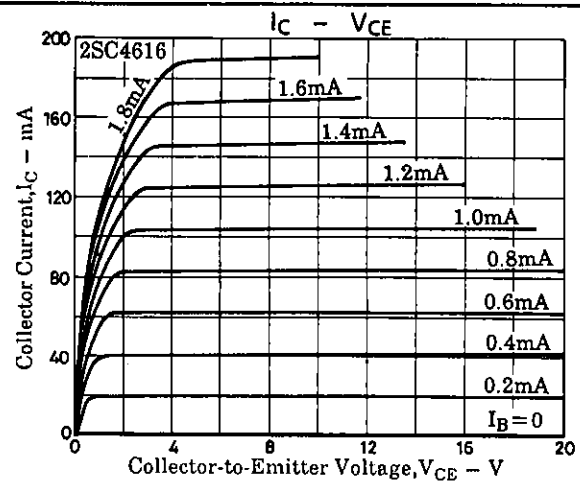
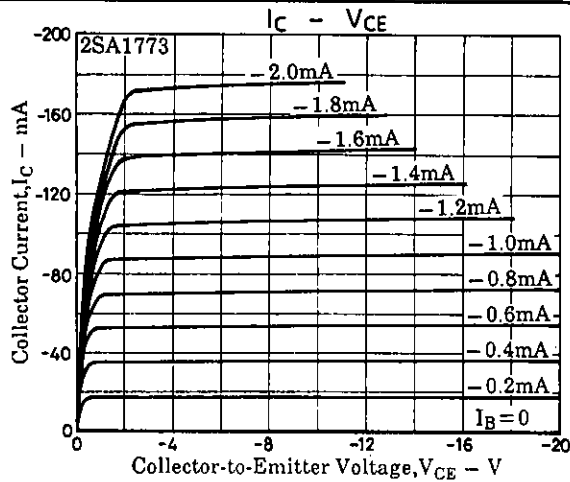


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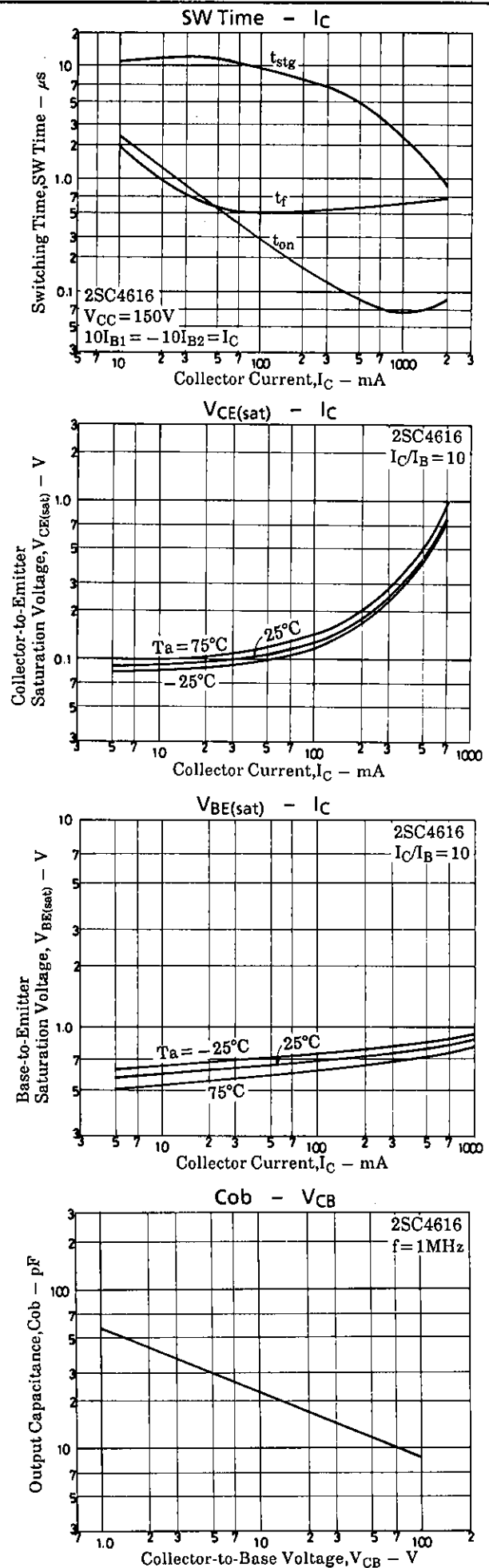
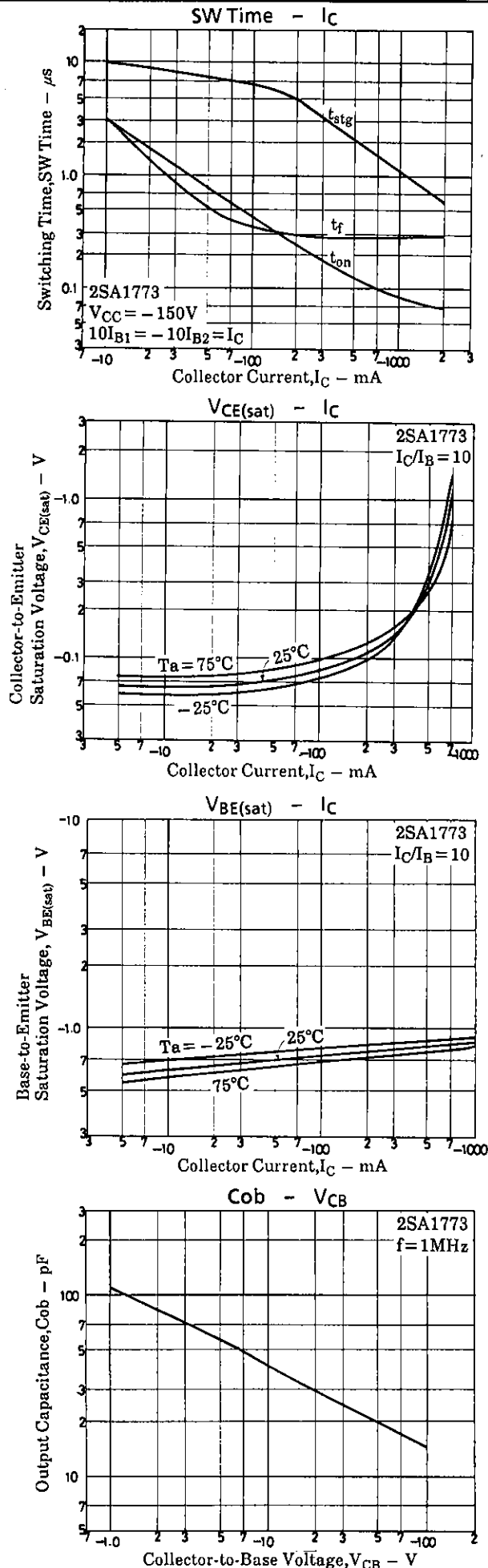
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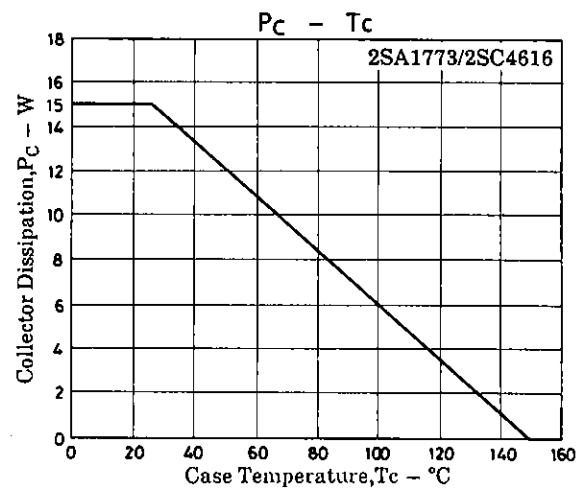
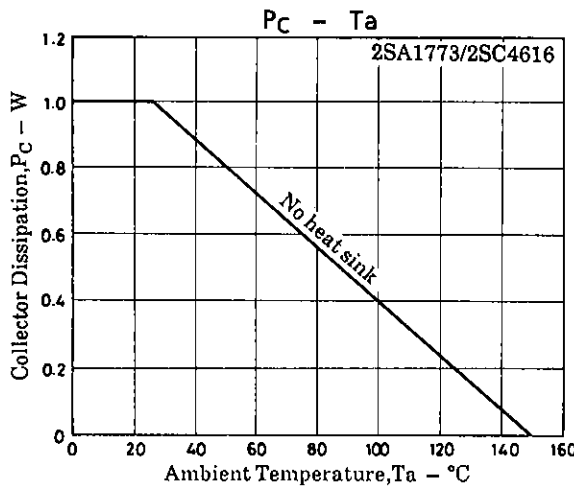
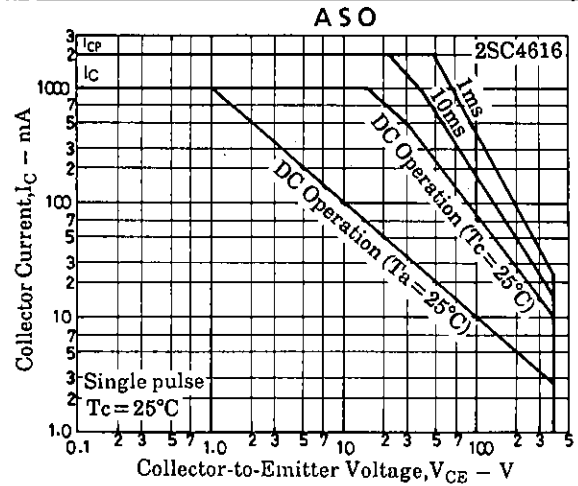
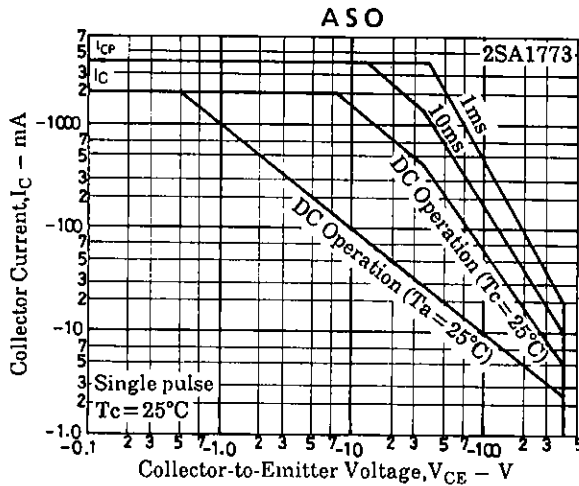
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